

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Please replace the paragraphs that begin on line 21 of page 2 and end on line 25 of page 4 with the following paragraph:

*A2*

A pattern correcting method of a mask for manufacturing a semiconductor device according to an aspect of the present invention comprises extracting a correction portion to be corrected from a mask pattern on the mask, obtaining a surrounding environment of the correction portion, and giving a variable correction amount to the correction portion in accordance with the surrounding environment.

**IN THE ABSTRACT:**

Please delete the Abstract in its entirety and replace it with the Abstract shown on the page attached to this Amendment.

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